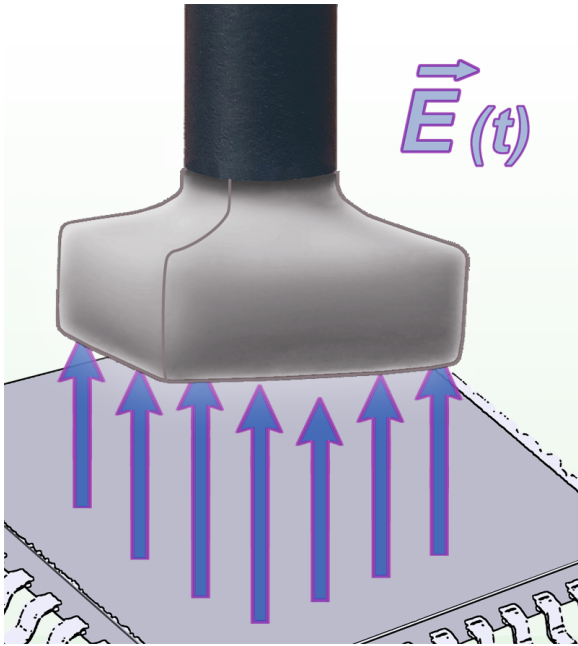


# XF-E 09s

E-Field Probe 30 MHz up to 6 GHz



## Short description

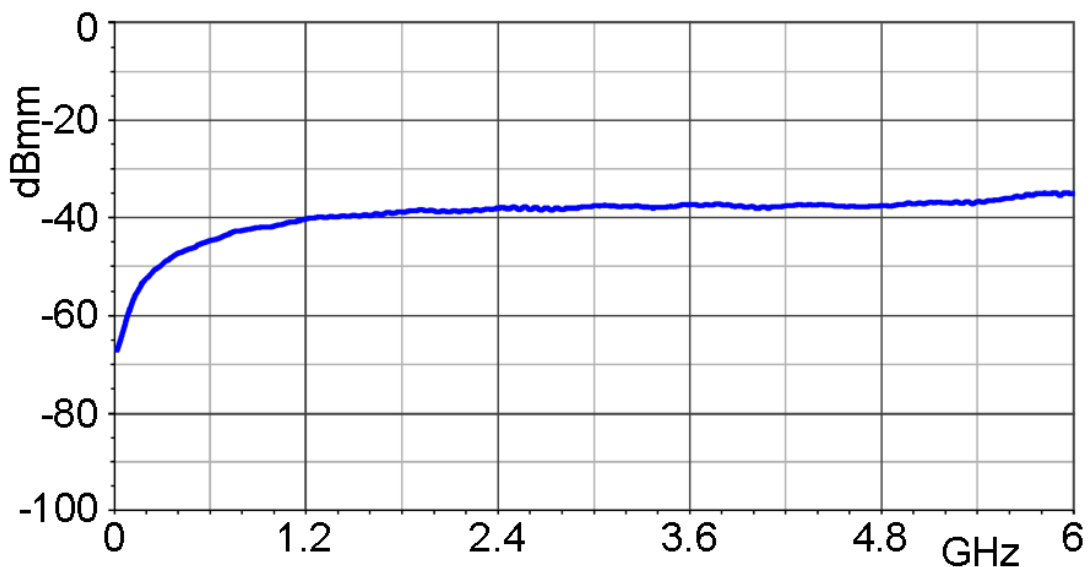
The electrode on the probe head of the XF-E 09s near-field probe detects electrical fields which, for example are decoupled above the IC's surface. The probe's resolution allows for measurements at a distance of 0.5 mm upto 10 mm above an assembly.

The XF-E 09s is a passive near-field probe. In principle it has the same structure as the XF-E 04s probe. To measure, the E-field probe is positioned above or onto components and printed circuit boards. It has a current attenuating sheath and, therefore, its upper half is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50  $\Omega$  input. The E-field probe has an internal terminating resistance.

## Technical parameters

|                       |                             |
|-----------------------|-----------------------------|
| Frequency range       | 30 MHz ... 6 GHz            |
| Probe head dimensions | $\approx (10 \times 10)$ mm |
| Connector - output    | SMA, female, jack           |

Frequency response [dB $\mu$ V] / [dB $\mu$ V/mm]



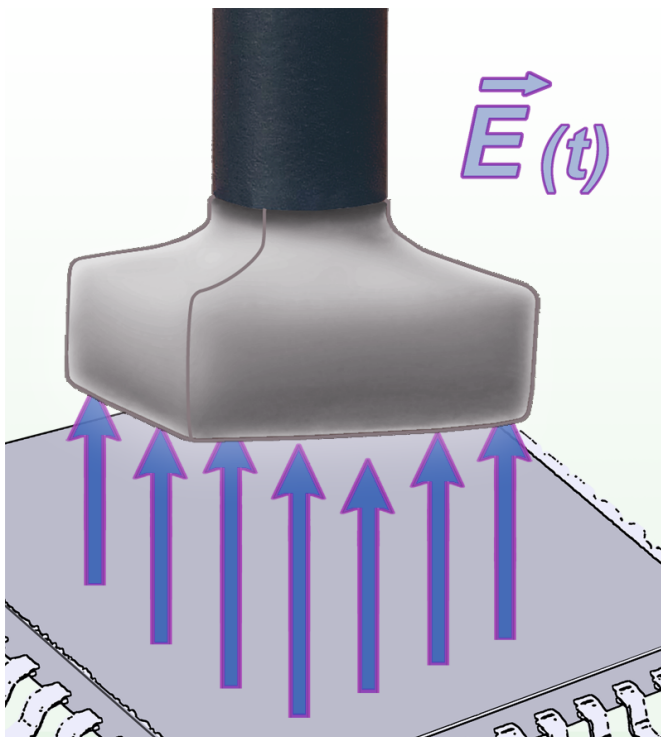
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E- field correction curve [dB $\mu$ V/mm] / [dB $\mu$ V]



Measuring principles



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Probe head

